Switch-mode Power Rectifier

DPAK Surface Mount Package

MBRD835L, SBRD8835L

This switch-mode power rectifier which uses the Schottky Barrier principle with a proprietary barrier metal, is designed for use as output rectifiers, free wheeling, protection and steering diodes in switching power supplies, inverters and other inductive switching circuits.

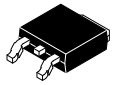
Features

- Low Forward Voltage
- 150 °C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Compact Size
- Lead Formed for Surface Mount
- SBRD8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

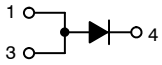
Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260 °C Max. for 10 Seconds
- Shipped 75 Units Per Plastic Tube
- ESD Rating:
  - Machine Model = C (> 400 V)
  - Human Body Model = 3B (> 8000 V)

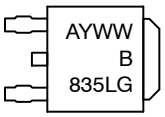
SCHOTTKY BARRIER RECTIFIER 8.0 AMPERES, 35 VOLTS



DPAK
CASE 369C



MARKING DIAGRAM



B835LG	= Specific Device Number
A	= Assembly Location*
Y	= Year
WW	= Work Week
G	= Pb-Free Device

* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

ORDERING INFORMATION

Device	Package	Shipping†
MBRD835LT4G	DPAK (Pb-Free)	2500 / Tape & Reel
SBRD8835LT4G-VF01	DPAK (Pb-Free)	2500 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	V
Average Rectified Forward Current (T_C = 88 °C)	$I_{F(AV)}$	8.0	A
Peak Repetitive Forward Current (Square Wave, Duty = 0.5, T_C = 80 °C)	I_{FRM}	16	A
Non−Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	75	A
Repetitive Avalanche Current (Current Decaying Linearly to Zero in 1 μs, Frequency Limited by T_{Jmax})	I_{AR}	2.0	A
Storage / Operating Case Temperature	T_{stg}	−65 to +150	°C
Operating Junction Temperature (Note 1)	T_J	−65 to +150	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance − Junction-to-Case	$R_{\theta JC}$	2.8	°C/W
Thermal Resistance − Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	°C/W

2. Rating applies when surface mounted on the minimum pad size recommended.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) (i_F = 8 Amps, T_C = +25 °C) (i_F = 8 Amps, T_C = +125 °C)	V_F	 0.51 0.41	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T_C = +25 °C) (Rated dc Voltage, T_C = +100 °C)	I_R	 1.4 35	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

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TYPICAL CHARACTERISTICS

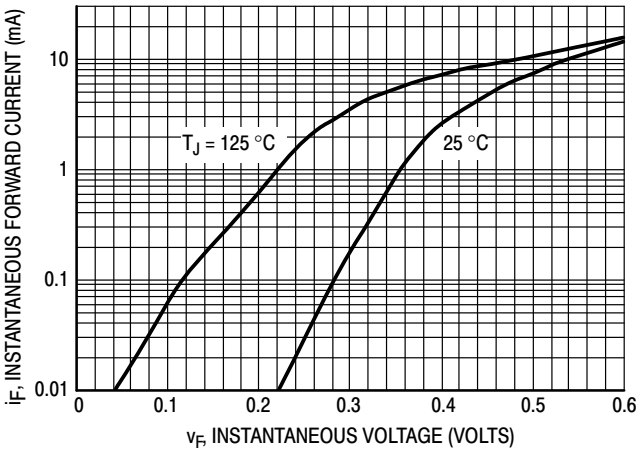


Figure 1. Maximum Forward Voltage

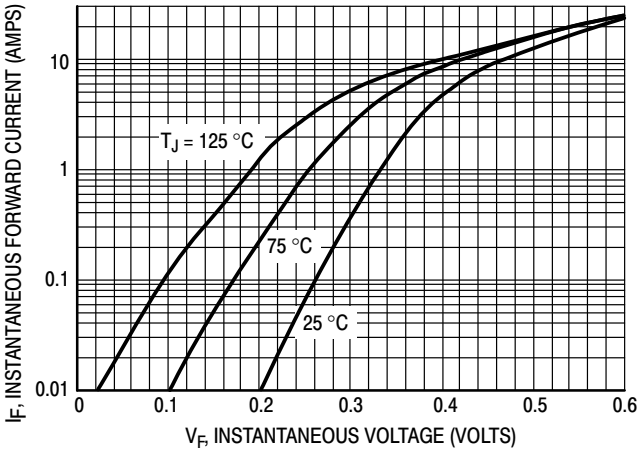


Figure 2. Typical Forward Voltage

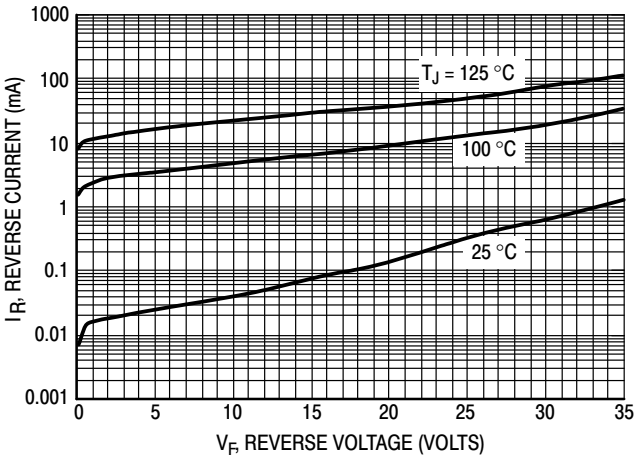


Figure 3. Maximum Reverse Current

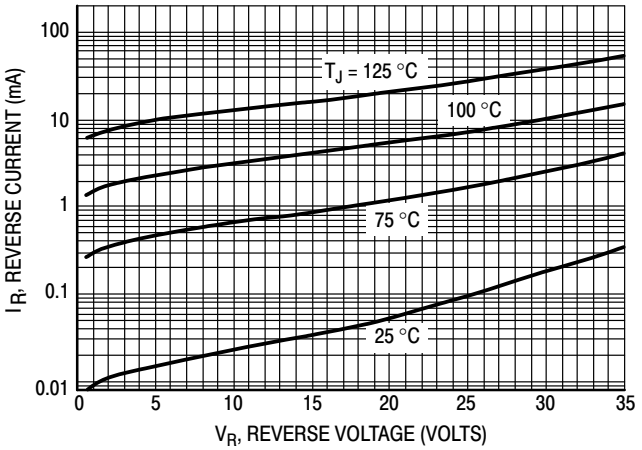


Figure 4. Typical Reverse Current

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TYPICAL CHARACTERISTICS

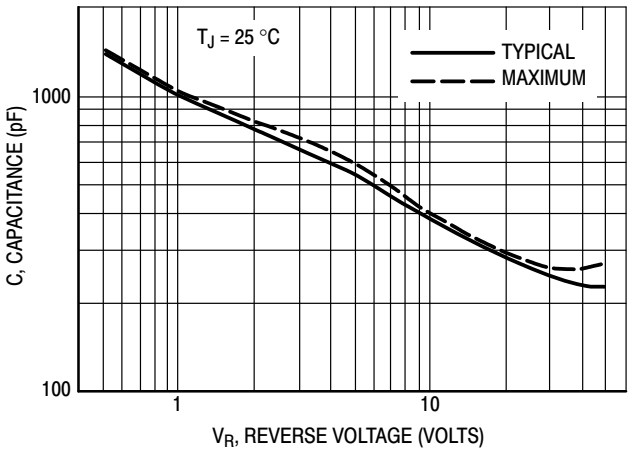


Figure 5. Maximum and Typical Capacitance

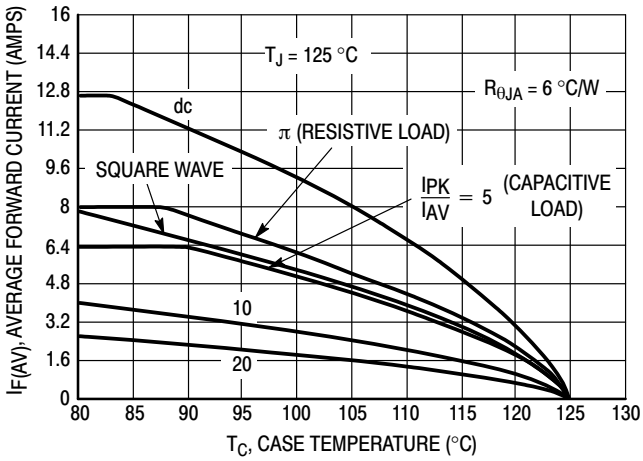


Figure 6. Current Derating, Infinite Heatsink

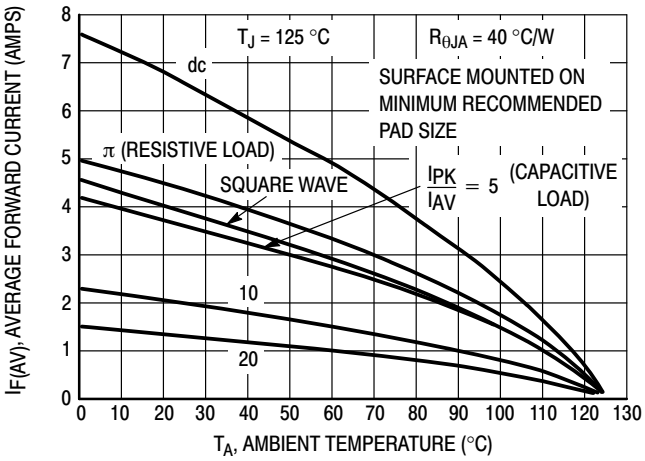


Figure 7. Current Derating

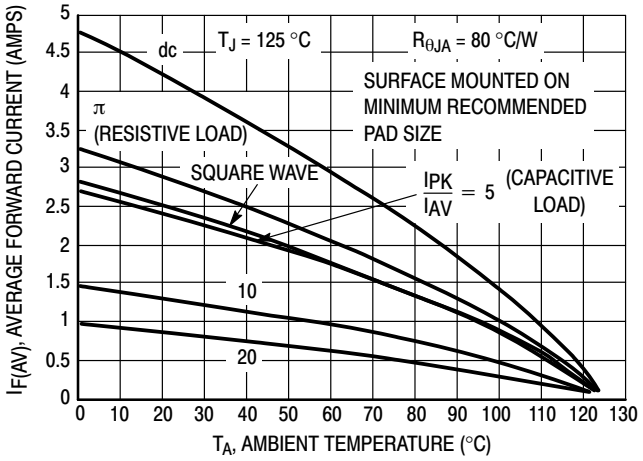


Figure 8. Current Derating, Free Air

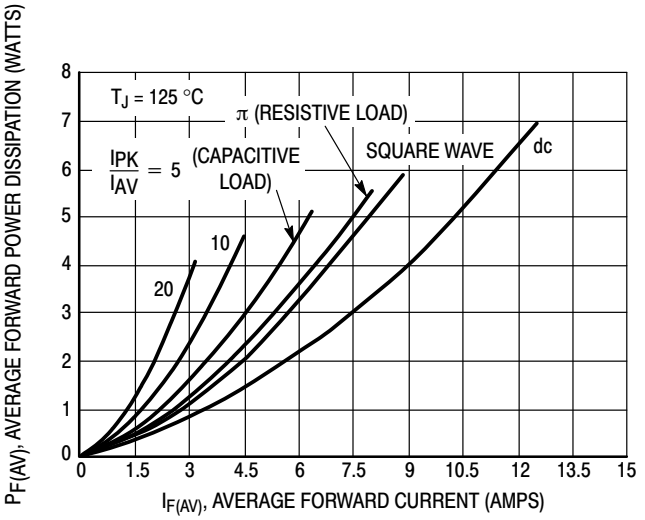


Figure 9. Forward Power Dissipation

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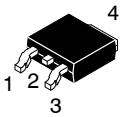
REVISION HISTORY

Revision	Description of Changes	Date
14	MBRD835LG, SBRD8835LG, SBRD8835LG-VF01, SBRD835LT4G-VF01, SBRD8835LT4G OPN Marked as Discontinued + Rebranded the Data Sheet to **onsemi** format	7/4/2025
15	Removal of discontinued devices (MBRD835LG, SBRD8835LG, SBRD8835LG-VF01, SBRD835LT4G-VF01, SBRD8835LT4G) from the data sheet	12/16/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

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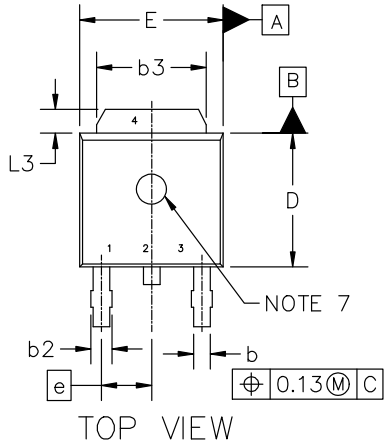
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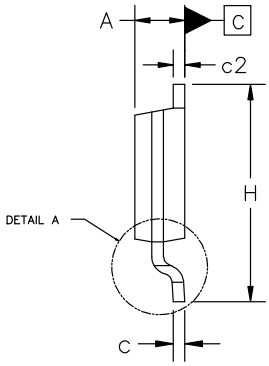
SCALE 1:1

DPAK−3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE L

DATE 24 AUG 2026

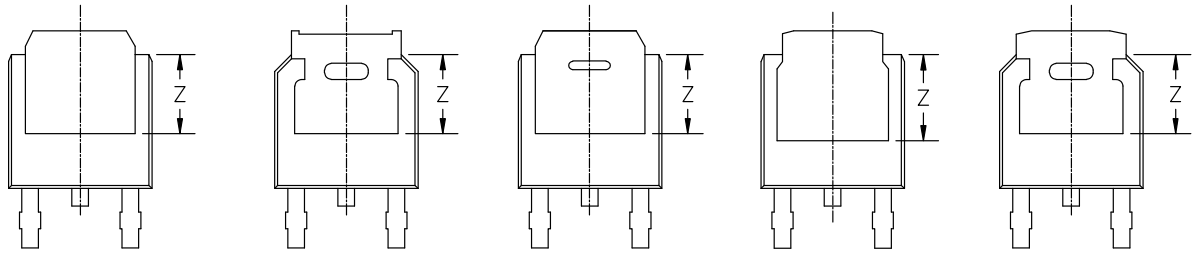


TOP VIEW



SIDE VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	2.18	2.28	2.38
A1	0.00	−−−	0.13
b	0.63	0.76	0.89
b2	0.72	0.93	1.14
b3	4.57	5.02	5.46
c	0.46	0.54	0.61
c2	0.46	0.54	0.61
D	5.97	6.10	6.22
E	6.35	6.54	6.73
e	2.29 BSC		
H	9.40	9.91	10.41
L	1.40	1.59	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	−−−	1.27
L4	−−−	−−−	1.01
Z	3.93	−−−	−−−

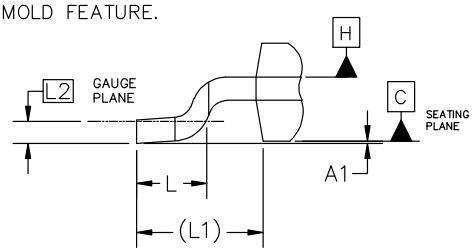


BOTTOM VIEW

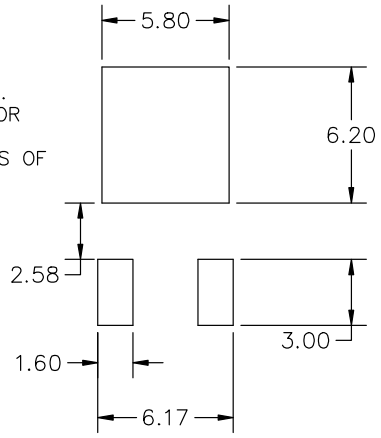
ALTERNATE CONSTRUCTIONS

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.



DETAIL A
ROTATED 90° CW



RECOMMENDED MOUNTING FOOTPRINT*
*For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques reference manual, SOLDERRM/D.

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DESCRIPTION:	**DPAK−3 6.10x6.54x2.28, 2.29P**	**PAGE 1 OF 2**

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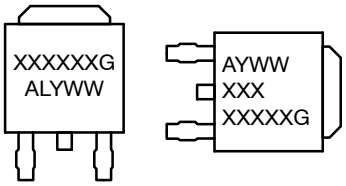
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DPAK−3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE L

DATE 24 AUG 2026

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX	= Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

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